

Silicon Variable Capacitance Diode

- For FM radio tuner with extended frequency band
- High tuning ratio at low supply voltage (car radio)
- Monolitic chip (common cathode) for perfect dual diode tracking
- Good linearity for C- V curve
- High figure of merit
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



BB914

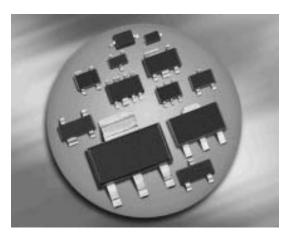


Туре	Package	Configuration	L_S (nH)	Marking
BB914	SOT23	common cathode	1.8	SM

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	18	V
Peak reverse voltage	V _{RM}	20	
($R \ge 5 \mathrm{k}\Omega$)			
Forward current	I _F	50	mA
Operating temperature range		-55 125	°C
Storage temperature	T _{stg}	-55 150	

¹Pb-containing package may be available upon special request





Parameter	Symbol		Values		
		min.	typ.	max.	1
DC Characteristics	·			-	
Reverse current	I _R	-	-		nA
<i>V</i> _R = 16 V		-	-	20	
$V_{\rm R}$ = 16 V, $T_{\rm A}$ = 85 °C				200	
AC Characteristics					
Diode capacitance	CT				pF
$V_{\rm R}$ = 2 V, f = 1 MHz		42.5	43.75	45	
$V_{R} = 8 V, f = 1 MHz$		17.6	18.7	19.75	
Capacitance ratio	C _{T2} /C _{T8}	2.28	2.34	2.42	
$V_{\rm R} = 2 \text{ V}, V_{\rm R} = 8 \text{ V}, f = 1 \text{ MHz}$					
Capacitance matching ¹⁾	$\Delta C_{T}/C_{T}$	-	-	1.5	%
$V_{\rm R} = 2 \text{ V}, V_{\rm R} = 8 \text{ V}, f = 1 \text{ MHz}$					
Series resistance	r _S	-	0.28	-	Ω
<i>V</i> _R = 2 V, <i>f</i> = 100 MHz					

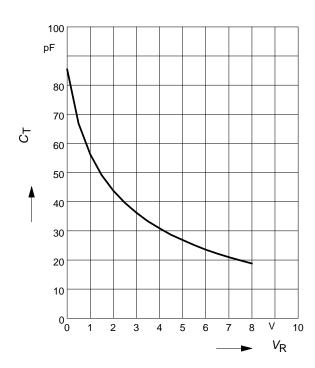
Electrical Characteristics at $T_A =$	= 25°C, unless otherwise specified
--	------------------------------------

¹For details please refer to Application Note 047.

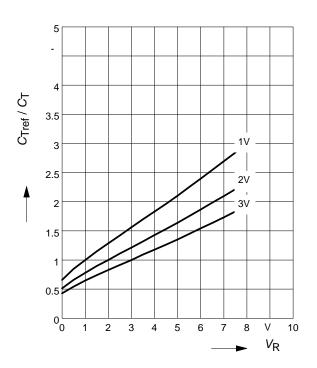


Diode capacitance $C_{T} = f(V_{R})$

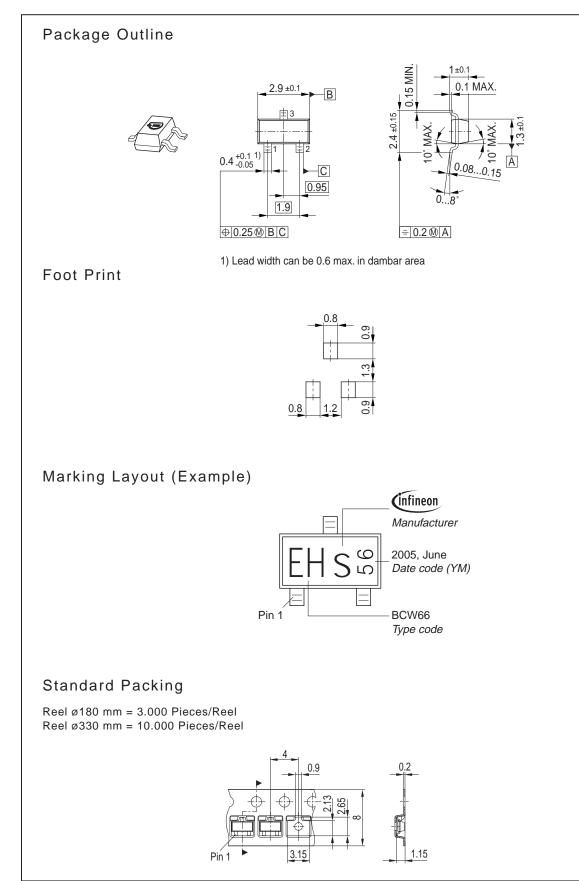
f = 1 MHz



Capacitance ratio $C_{\text{Tref}}/C_{\text{T}} = f(V_{\text{R}})$ f = 1MHz









Edition 2006-02-01 Published by Infineon Technologies AG 81726 München, Germany © Infineon Technologies AG 2007. All Rights Reserved.

Attention please!

The information given in this dokument shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.